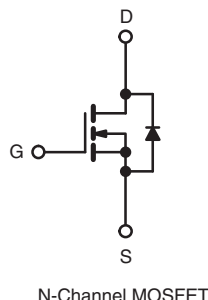
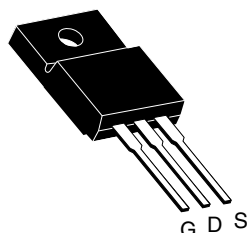


E Series Power MOSFET

PRODUCT SUMMARY

V_{DS} (V) at T_J max.	650	
$R_{DS(on)}$ max. at 25 °C (Ω)	$V_{GS} = 10$ V	0.125
Q_g max. (nC)	130	
Q_{gs} (nC)	15	
Q_{gd} (nC)	39	
Configuration	Single	

TO-220 FULLPAK



FEATURES

- Low Figure-of-Merit (FOM) $R_{on} \times Q_g$
- Low Input Capacitance (C_{iss})
- Reduced Switching and Conduction Losses
- Ultra Low Gate Charge (Q_g)
- Avalanche Energy Rated (UIS)
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE
Available

APPLICATIONS

- Server and Telecom Power Supplies
- Switch Mode Power Supplies (SMPS)
- Power Factor Correction Power Supplies (PFC)
- Lighting
 - High-Intensity Discharge (HID)
 - Fluorescent Ballast Lighting
 - LED Lighting
- Industrial
 - Welding
 - Induction Heating
 - Motor Drives
- Battery Chargers
- Renewable Energy
 - Solar (PV Inverters)

ORDERING INFORMATION

Package	TO-220 FULLPAK
Lead (Pb)-free and Halogen-free	SiHF30N60E-GE3
Lead (Pb)-free	SiHF30N60E-E3

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	600	V
Gate-Source Voltage	V_{GS}	± 20	
Gate-Source Voltage AC ($f > 1$ Hz)		30	
Continuous Drain Current ($T_J = 150$ °C) ^d	V_{GS} at 10 V	$T_C = 25$ °C	A
		$T_C = 100$ °C	
Pulsed Drain Current ^a	I_{DM}	65	
Linear Derating Factor		0.29	W/°C
Single Pulse Avalanche Energy ^b	E_{AS}	690	mJ
Maximum Power Dissipation	P_D	37	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 150	°C
Drain-Source Voltage Slope	dV/dt	37	V/ns
Reverse Diode dV/dt ^e		18	
Soldering Recommendations (Peak Temperature) ^c	for 10 s	300	°C

Notes

- Repetitive rating; pulse width limited by maximum junction temperature.
- $V_{DD} = 50$ V, starting $T_J = 25$ °C, $L = 28.2$ mH, $R_g = 25$ Ω , $I_{AS} = 7$ A.
- 1.6 mm from case.
- Limited by maximum junction temperature.
- $I_{SD} \leq I_D$, $dI/dt = 100$ A/ μ s, starting $T_J = 25$ °C.

THERMAL RESISTANCE RATINGS

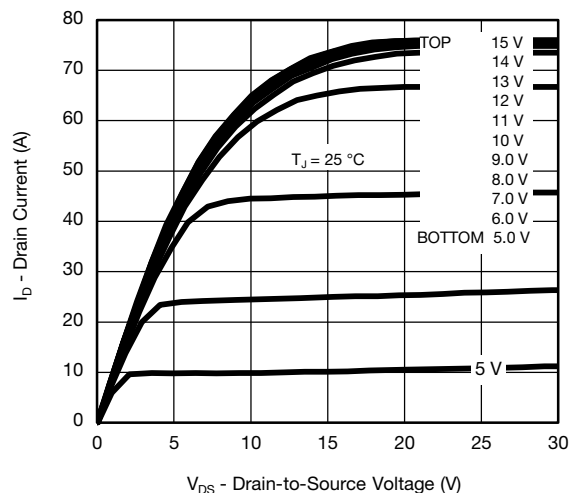
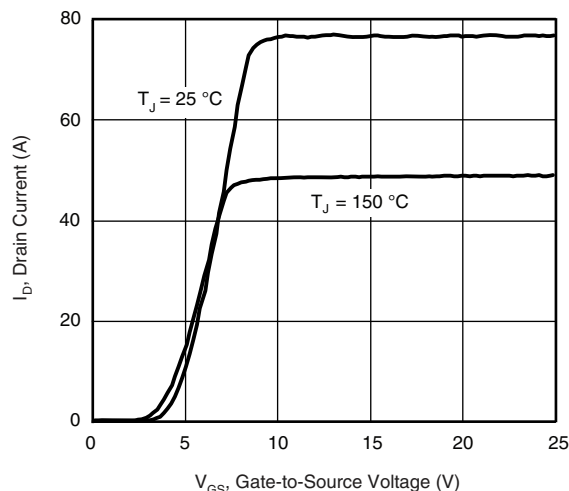
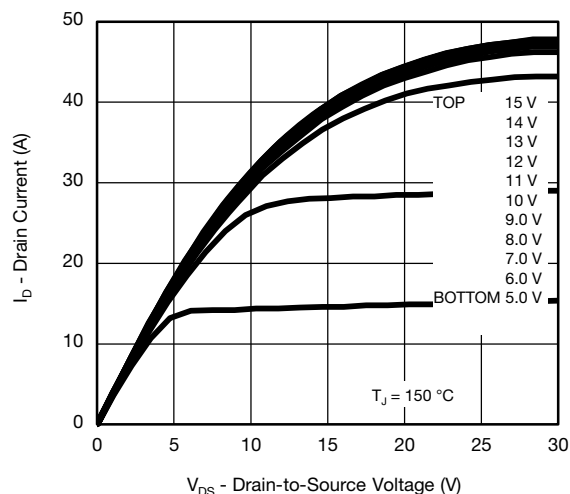
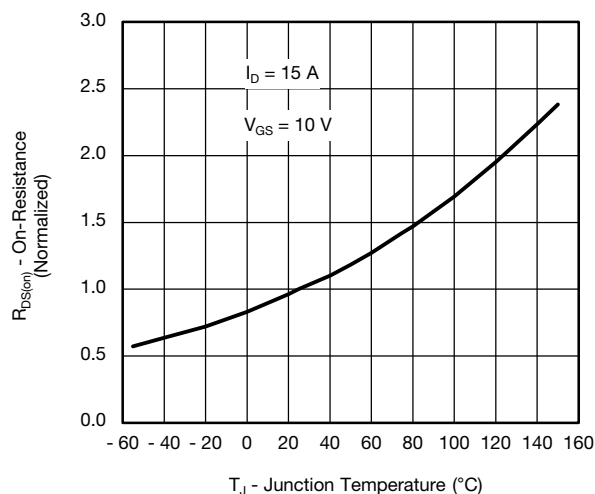
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	65	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	-	3.4	

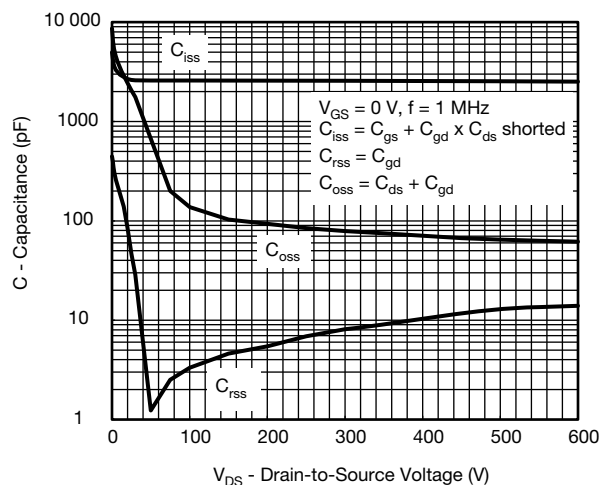
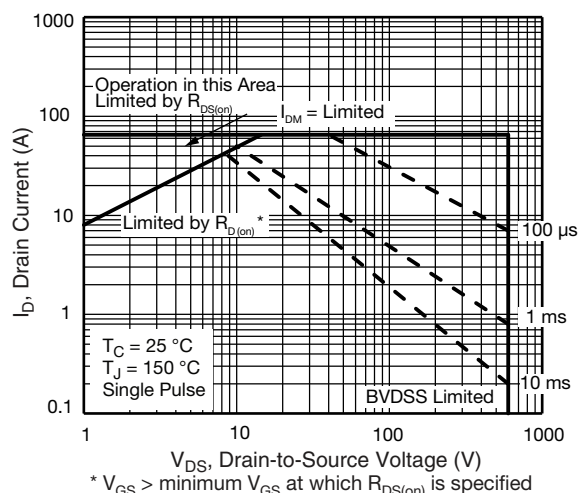
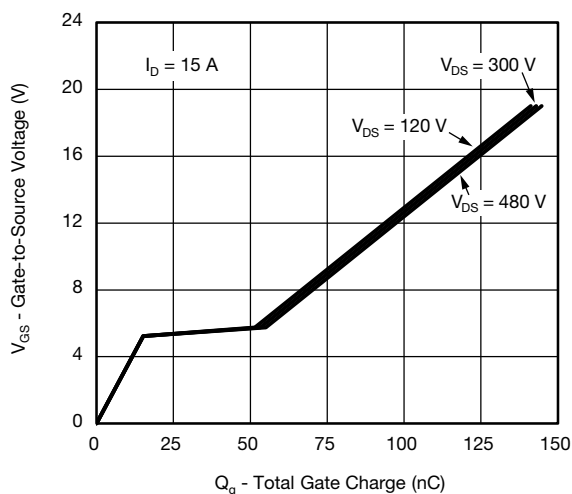
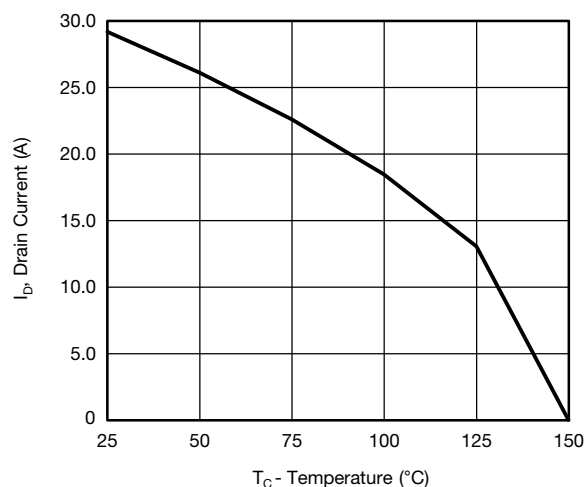
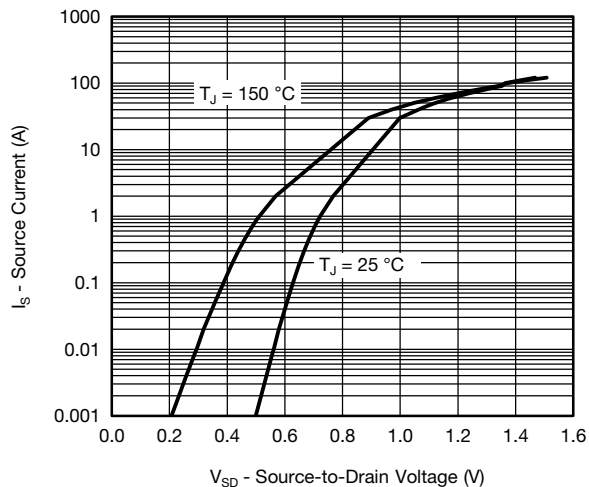
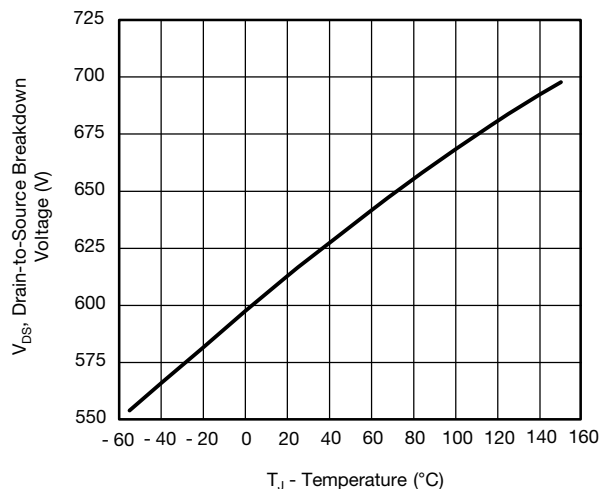
SPECIFICATIONS ($T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

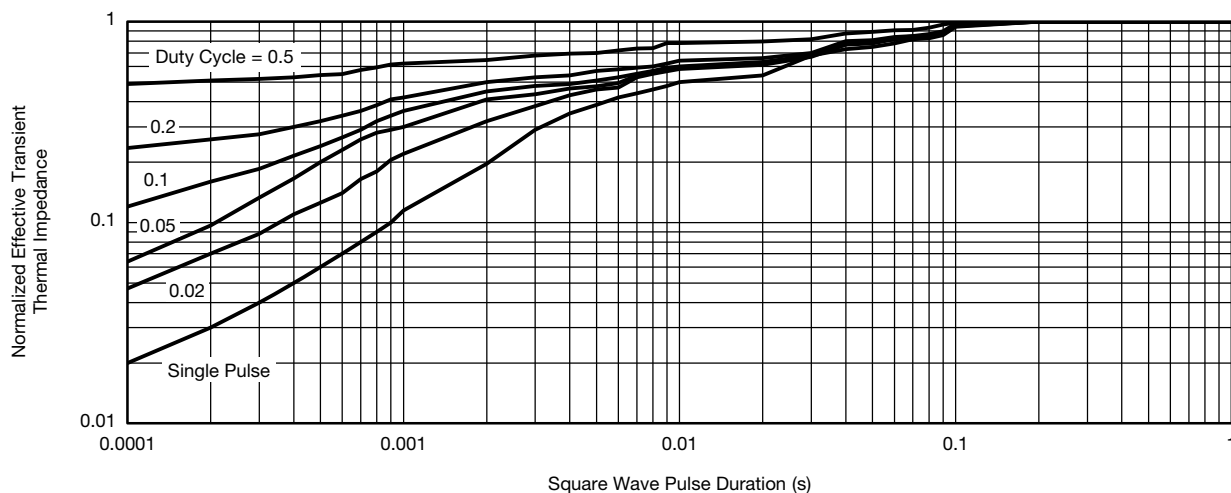
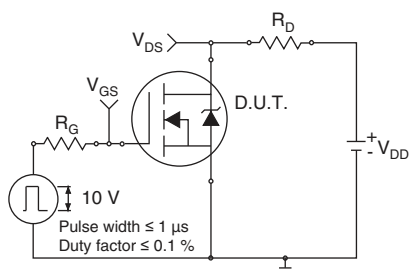
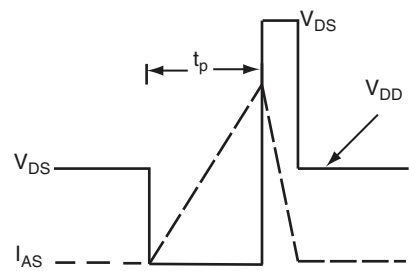
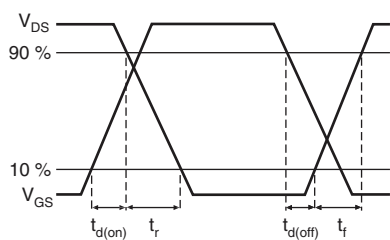
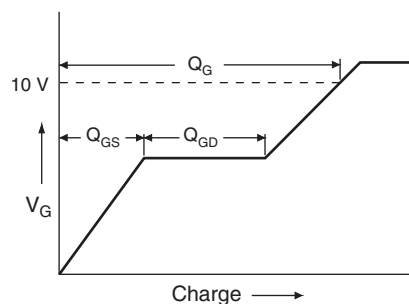
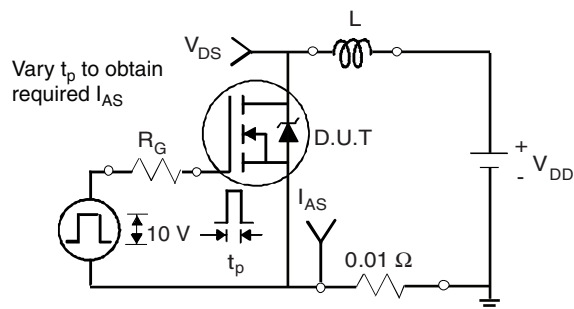
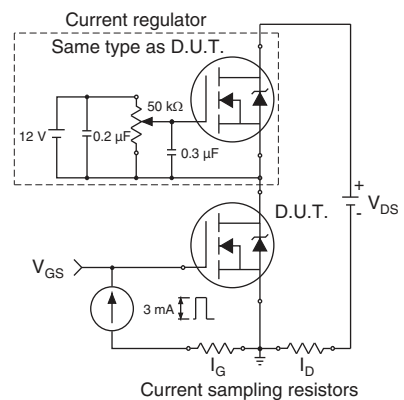
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$	600	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^{\circ}\text{C}$, $I_D = 250\text{ }\mu\text{A}$	-	0.64	-	V/°C
Gate-Source Threshold Voltage (N)	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2.0	-	4.0	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20\text{ V}$	-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 600\text{ V}$, $V_{GS} = 0\text{ V}$	-	-	1	μA
		$V_{DS} = 600\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 150\text{ }^{\circ}\text{C}$	-	-	100	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = 15\text{ A}$	-	0.104	0.125	Ω
Forward Transconductance ^a	g_{fs}	$V_{DS} = 8\text{ V}$, $I_D = 3\text{ A}$	-	5.4	-	S
Dynamic						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}$, $V_{DS} = 100\text{ V}$, $f = 1.0\text{ MHz}$	-	2600	-	pF
Output Capacitance	C_{oss}		-	138	-	
Reverse Transfer Capacitance	C_{rss}		-	3	-	
Effective Output Capacitance, Energy Related ^a	$C_{o(er)}$	$V_{DS} = 0\text{ V to } 480\text{ V}$, $V_{GS} = 0\text{ V}$	-	98	-	
Effective Output Capacitance, Time Related ^b	$C_{o(tr)}$		-	346	-	
Total Gate Charge	Q_g	$V_{GS} = 10\text{ V}$, $I_D = 15\text{ A}$, $V_{DS} = 480\text{ V}$	-	85	130	nC
Gate-Source Charge	Q_{gs}		-	15	-	
Gate-Drain Charge	Q_{gd}		-	39	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 380\text{ V}$, $I_D = 15\text{ A}$, $V_{GS} = 10\text{ V}$, $R_g = 4.7\text{ }\Omega$	-	19	40	ns
Rise Time	t_r		-	32	65	
Turn-Off Delay Time	$t_{d(off)}$		-	63	95	
Fall Time	t_f		-	36	75	
Gate Input Resistance	R_g	$f = 1\text{ MHz}$, open drain	-	0.63	-	Ω
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	29	A
Pulsed Diode Forward Current	I_{SM}		-	-	65	
Diode Forward Voltage	V_{SD}	$T_J = 25\text{ }^{\circ}\text{C}$, $I_S = 15\text{ A}$, $V_{GS} = 0\text{ V}$	-	-	1.3	V
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^{\circ}\text{C}$, $I_F = I_S = 15\text{ A}$, $dI/dt = 100\text{ A}/\mu\text{s}$, $V_R = 20\text{ V}$	-	402	605	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	7	15	μC
Reverse Recovery Current	I_{RRM}		-	32	65	A

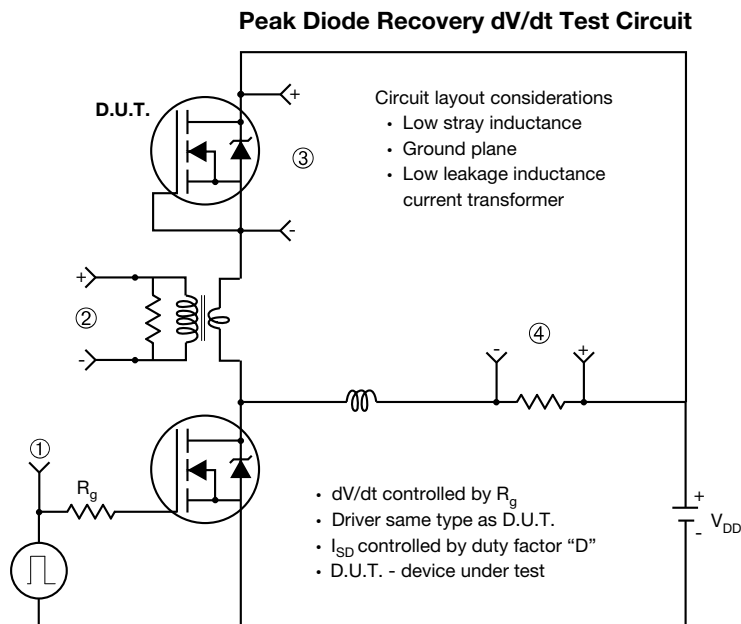
Notes

- a. $C_{oss(er)}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS} .
b. $C_{oss(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS} .

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Fig. 1 - Typical Output Characteristics, $T_C = 25^\circ\text{C}$

Fig. 3 - Typical Transfer Characteristics

Fig. 2 - Typical Output Characteristics, $T_C = 150^\circ\text{C}$

Fig. 4 - Normalized On-Resistance vs. Temperature


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

Fig. 8 - Maximum Safe Operating Area

Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

Fig. 9 - Maximum Drain Current vs. Case Temperature

Fig. 7 - Typical Source-Drain Diode Forward Voltage

Fig. 10 - Temperature vs. Drain-to-Source Voltage


Fig. 11 - Normalized Thermal Transient Impedance, Junction-to-Case

Fig. 12 - Switching Time Test Circuit

Fig. 15 - Unclamped Inductive Waveforms

Fig. 13 - Switching Time Waveforms

Fig. 16 - Basic Gate Charge Waveform

Fig. 14 - Unclamped Inductive Test Circuit

Fig. 17 - Gate Charge Test Circuit

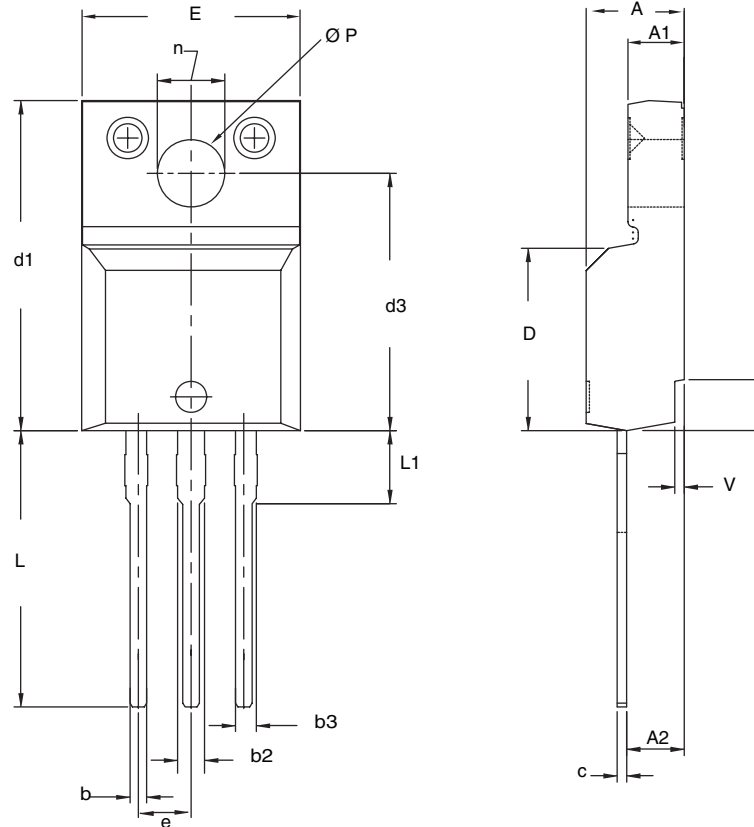

Note

a. $V_{GS} = 5 V$ for logic level devices

Fig. 18 - For N-Channel

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TO-220 FULLPAK (HIGH VOLTAGE)



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.570	4.830	0.180	0.190
A1	2.570	2.830	0.101	0.111
A2	2.510	2.850	0.099	0.112
b	0.622	0.890	0.024	0.035
b2	1.229	1.400	0.048	0.055
b3	1.229	1.400	0.048	0.055
c	0.440	0.629	0.017	0.025
D	8.650	9.800	0.341	0.386
d1	15.88	16.120	0.622	0.635
d3	12.300	12.920	0.484	0.509
E	10.360	10.630	0.408	0.419
e	2.54 BSC		0.100 BSC	
L	13.200	13.730	0.520	0.541
L1	3.100	3.500	0.122	0.138
n	6.050	6.150	0.238	0.242
Ø P	3.050	3.450	0.120	0.136
u	2.400	2.500	0.094	0.098
v	0.400	0.500	0.016	0.020

ECN: X09-0126-Rev. B, 26-Oct-09
DWG: 5972

Notes

1. To be used only for process drawing.
2. These dimensions apply to all TO-220, FULLPAK leadframe versions 3 leads.
3. All critical dimensions should C meet $C_{pk} > 1.33$.
4. All dimensions include burrs and plating thickness.
5. No chipping or package damage.



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<http://moschip.ru/get-element>

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